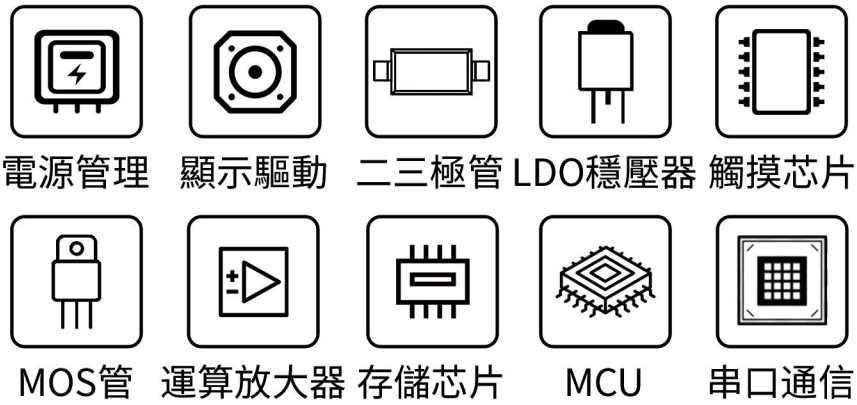
TDSEMIC
拓 電 半 導 體

自主封測 品質把控 售後保障

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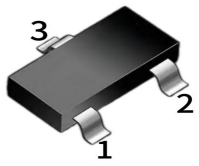
MMBD4148SE
D4-TD（0.23）

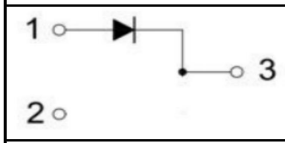
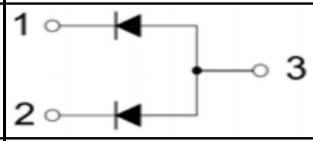
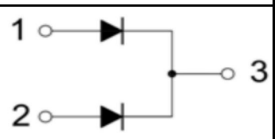
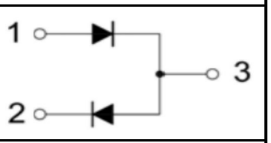
產品規格說明書

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

SOT-23
1.BASE
2.EMITTER
3.COLLECTOR



MMBD4148A	MMBD4148CA	MMBD4148CC	MMBD4148SE
			
MARKING:5H	MARKING:D6	MARKING:D5	MARKING:D4

Solid dot = Green molding compound device, if none, the normal device

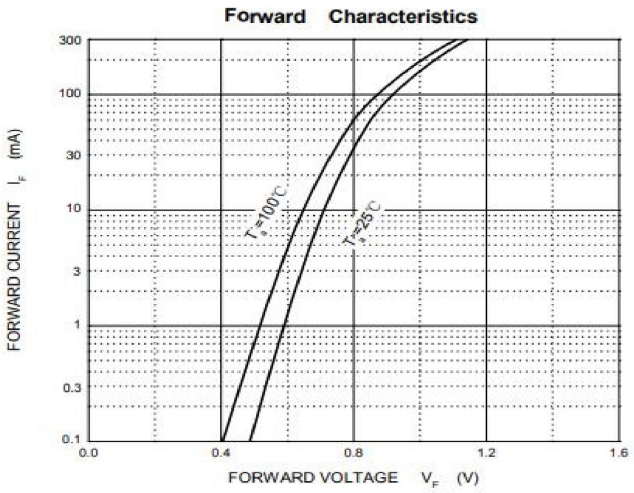
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

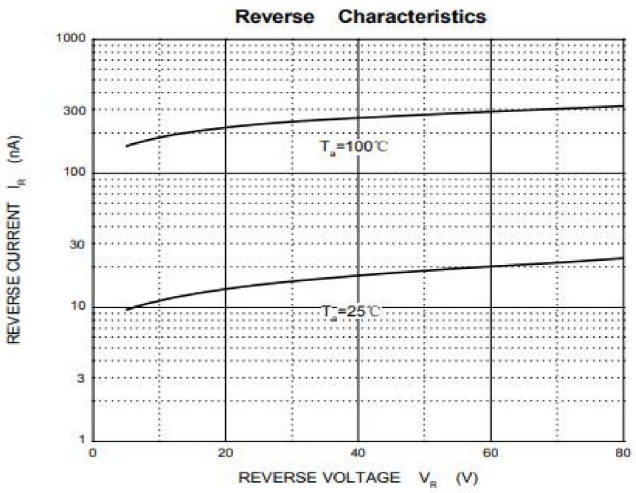
Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	VRM	100	V
Peak Repetitive Peak Reverse Voltage	VRRM	100	V
Working Peak Reverse Voltage	VRWM	100	V
DC Blocking Voltage	VR	100	V
RMS Reverse Voltage	VR(RMS)	72	V
Forward Continuous Current	IFM	300	mA
Average Rectified Output Current	Io	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	350	mW
Thermal Resistance from Junction to Ambient	RθJA	357	℃/W
Junction Temperature	TJ	150	℃
Storage Temperature Range	TSTG	-55~+150	℃

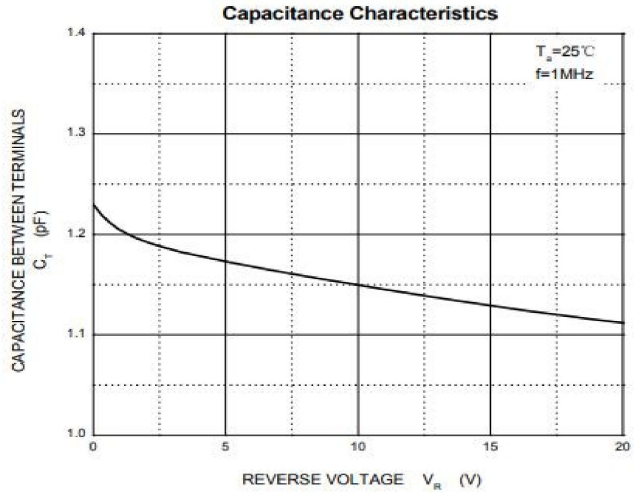
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

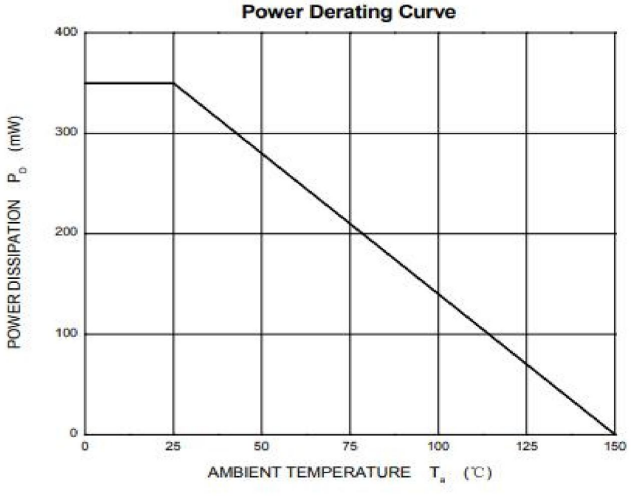
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)1	IR=100μA	100			V
	V(BR)2	IR=5μA	75			V
Forward voltage	VF	IF=10mA			1	V
Reverse current	IR1	VR=75V			5	uA
	IR2	VR=25V			25	nA
Capacitance between terminals	Ctot	VR=0V,f=1MHz			4	pF
Reverse recovery time	t r r	IF=IR=10mA,VR=6V Irr=0.1XIR,RL= 100			4	nS

Typical Electrical and Thermal Characteristics

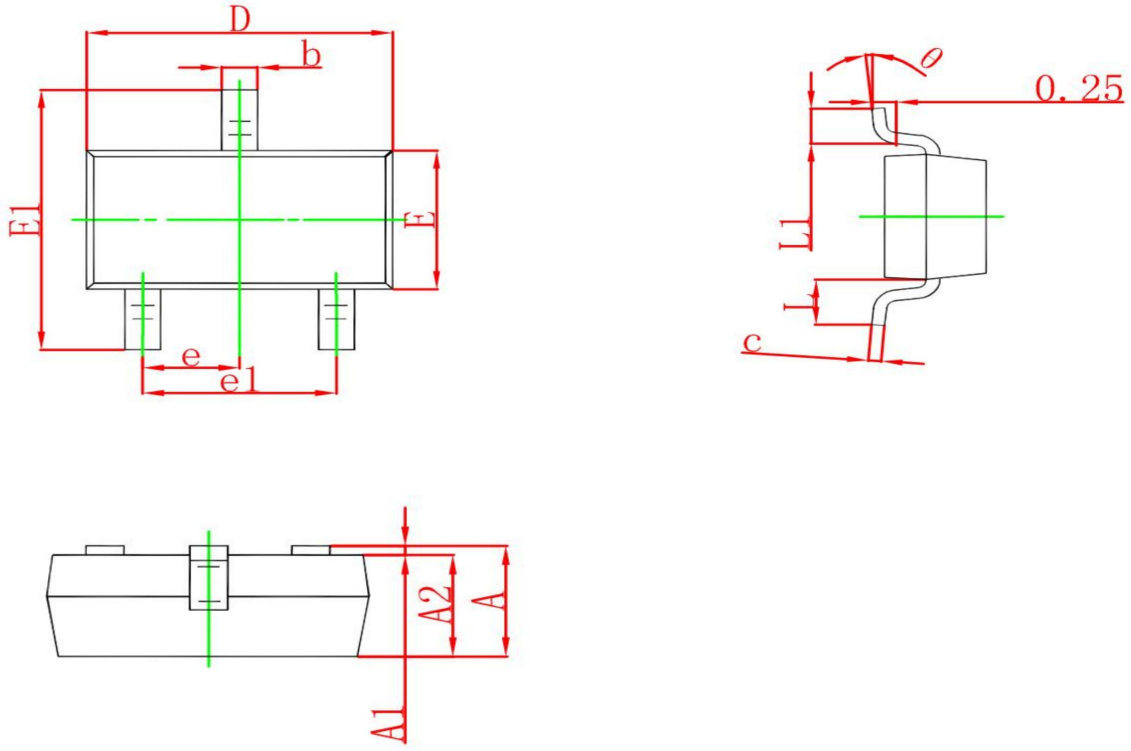








SOT-23 Package Outline Dimesions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°